Doping dependance of the spin resonance peak in bilayer high-T_c superconductors

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(D ated: M arch 23, 2024)

M otivated by a recent experiment on the bilayer Y $_1$ $_x$ C $_x$ B $_a$ C $_y$ Superconductor and based on a bilayer t $_y$ m odel, we calculate the spin susceptibility at dierent doping densities in the even and odd channels in a bilayer system . It is found that the intensity of the resonance peak in the even channel is much weaker than that in the odd one, with the resonance position being at a higher frequency. While this dierence decreases as the doping increases, and both the position and amplitude of the resonance peaks in the two channels are very similar in the deeply overdoped sample. Moreover, the resonance frequency in the odd channel is found to be linear with the critical temperature T_c , while the resonance frequency increases as doping decreases in the even channel and tends to saturate at the underdoped sample. We elaborate the results based on the Ferm i surface topology and the d-wave superconductivity.

PACS num bers: 74.25 Ha, 74.20 Mn, 71.10 Fd

I. INTRODUCTION

Inelastic neutron scattering (INS) experiments have been playing an important role in the studies of the spin dynamics of high-T_c superconductors. They can provide direct information of the momentum and frequency dependence of the dynamical spin susceptibility. Over the past decade, one of the most striking features observed in the INS experiments is the resonant spin excitation. The resonance peak, which has been found in several classes of cuprate m aterials [1, 2, 3, 4, 5], has attracted m uch experim ental and theoretical attention. This peak is centered at the momentum (;), with its intensity decreasing rapidly when the frequency moves away from (;). The resonance frequency is found to be in proportional to the critical tem perature [4, 5, 6]. Theoretically, the origin of the spin resonance and its role on superconductivity are still open questions [7, 8, 9, 10, 11, 12, 13]. It has been proposed that the spin resonance is a collective spin excitation mode [13, 14, 15, 16, 17, 18, 19, 20]. Based on this scenario, many properties of spin uctuations observed in the INS experim ents have be explained consistently.

In the YBa₂Cu₃O_y (YBCO) and Bi₂Sr₂CaCu₂O_{8+x} (Bi-2212) fam ily, one unit cell contains two CuO₂ planes. The electronic states in di erent CuO₂ layers belonging to one cell are strongly coupled at all doping levels. Thus, two modes ofmagnetic excitation are expected to exist in the bilayer systems, i.e., one in the even channel and the other in the odd channel according to the symmetry with respect to the exchange of the layers [21, 22, 23, 24]. In earlier experiments, this expectation was only conmed in the insulating YBCO samples [25]. In the superconducting state, the spin resonance mode was not observed in the even channel, presumably due to a much weaker intensity in this channel. Recently, the instrumentation

advances have made it possible to resolve weaker features in the INS experiments. Two distinct resonance modes were observed in the superconducting state of bilayer $(Y,Ca)Ba_2Cu_3O_y$ samples [26, 27]. It was found that the resonance peak intensity in the even channel (I^e) is much weaker than that in the odd channel (I^o) , and the resonance frequency is higher than that of the odd channel. Very recently, the doping evolution of the resonance peak in both the even and odd channels of $(Y,Ca)Ba_2Cu_3O_y$ was studied in detail by the INS experim ents [28]. In the overdoped samples (y = 7), the resonance position of the odd channel is close to that of the even channel. At this doping level, the two resonance m odes have also closer intensities ($I^e=I^o=0.4$). When the doping density decreases, the doping evolution of the resonance frequency in the odd channel seems to follow a similar doping dependence as T_c, while the resonance frequency seems to keep increasing in the even channel as the doping decreases and saturates to a constant in the underdoped sample. Moreover, the resonance peak intensity in the odd channel is also much larger than that in the even channel in the underdoped sample. The intensity ratio Ie=Io decreases monotonously as doping decreases and reaches 0.05 in strongly underdoped sam -

M otivated by these experim ental observations, we here present a detailed investigation of the doping dependence of the spin resonance mode in the even and odd channels. Following Ref. [29], we employ a bilayert $\,$ J type H amiltonian including the interlayer hopping and interlayer exchange coupling. In order to exam ine the robustness of the doping dependance of the dierence between the two resonance modes, we also look into in detail the elect of the interlayer hopping parameters t_2 and the interlayer exchange coupling J_2 .

The article is organized as follows. In Sec. II, we

introduce the m odel and work out the form alism . In Sec. III, we perform numerical calculations and discuss the obtained results. Finally, we give a brief summary in Sec. IV .

II. HAM ILTONIAN AND FORMALISM

We start with a Hamiltonian which describes a system with two layers per unit cell.

where l=1;2 denotes the layer index. In the slave-boson approach, the physical electron operators $c_i^{(l)}$ are expressed by slave bosons $b_i^{(l)}$ carrying the charge and ferm ions $f_i^{(l)}$ representing the spin, $c_i^{(l)}=b_i^{(l)y}f_i^{(l)}$. At the mean-eld level, we consider the order parameters $_{ij}^{(l)}=hf_{i''}^{(l)}f_{j''}^{(l)}$ if $_{i\#}^{(l)}f_{j''}^{(l)}$ if $_{i\#}^{$

Then, the mean-eld Hamiltonian can be written as,

$$H_{m} = \begin{array}{c} X \\ \mathbf{H}_{m} \\ \mathbf{X} \\ \mathbf{X} \\ \mathbf{X} \\ \mathbf{X} \\ \mathbf{X} \\ \mathbf{E}_{?} \\ \mathbf{E}_{?} \\ \mathbf{E}_{?} \\ \mathbf{E}_{?} \\ \mathbf{X} \\ \mathbf{E}_{?} \\ \mathbf{E}_{?} \\ \mathbf{X} \\ \mathbf{E}_{?} \\ \mathbf{E}_{?}$$

with " $_k$ = 2(t + J 0 $_0$)(cosk $_x$ + cosk $_y$) 4 th cosk $_x$ cosk $_y$, $_k$ = 2J 0 $_0$ (cosk $_x$ cosk $_y$), " $_0$ = 4N J 0 ($_0^2$ + $_0^2$), and J 0 = 3J=8. Diagonalizing the Ham iltonian, we can get the antibonding band (A) and bonding band (B) with the dispersion $_k$ = " $_k$ t $_2$. Here we use the momentum independent interlayer hopping constant t $_2$, being consistent with the recent angle resolved photoem ission experiment on YBCO [30], which reveals an obvious bilayer splitting along the nodal direction.

The bare spin susceptibility can be expressed as,

$$(; \circ) (q; !) = \frac{1}{N} \sum_{k}^{X} f^{\frac{1}{4}} (1 - \frac{(\circ) (\circ) + k - k + q}{E_{k} + q})$$

$$[\frac{1 - f(E_{k+q}^{(\circ)}) - f(E_{k}^{(\circ)})}{! + (E_{k+q}^{(\circ)} + E_{k}^{(\circ)}) + i} - \frac{1 - f(E_{k+q}^{(\circ)}) - f(E_{k}^{(\circ)})}{! - (E_{k+q}^{(\circ)} + E_{k}^{(\circ)}) + i}]$$

$$+ \frac{1}{2} [1 + \frac{(\circ) (\circ) + k - k - k + q}{E_{k} + q}] \frac{f(E_{k+q}^{(\circ)}) - f(E_{k}^{(\circ)})}{E_{k+q}^{(\circ)} - E_{k}^{(\circ)}) + i} g(3)$$

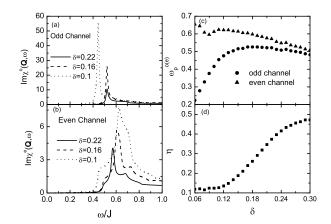


FIG. 1: Panels (a) and (b) are the imaginary parts of the spin susceptibility versus the frequency for the wave vector Q=(;) with $t_2=0.1J$, $J_2=0.15J$ in the odd and even channels, respectively. Panel (c) is the resonance position as a function of the doping. Panel (d) is the intensity ratio of the spin susceptibilities between the even and odd channels. The quasiparticle damping =0.01.

Here; ${}^0=A$; B, $E_k^{()}=\frac{q}{k}+\frac{2}{k}$ is the quasiparticle energy, and f(!) is the Ferm i distribution function.

The bare even and odd channel spin susceptibilities which come respectively from the intraband and interband electronic transitions, are given by

$${\overset{\text{e}}{_{0}}} (q;!) = {\overset{(A;A)}{_{;A}}} (q;!) + {\overset{(B;B)}{_{;A}}} (q;!);$$

$${\overset{\text{o}}{_{0}}} (q;!) = {\overset{(A;B)}{_{;B}}} (q;!) + {\overset{(B;A)}{_{;A}}} (q;!);$$

$$(4)$$

By including the correction of the antiferrom agnetic (AF) spin uctuations to the spin susceptibility in the form of the random phase approximation (RPA), the renormalized spin susceptibilities for the even and odd channels can be obtained as

$$e^{(0)}(q;!) = \frac{e^{(0)}(q;!)}{1 + (eJ_q J_?) e^{(0)}(q;!) = 2}; (5)$$

where signs represent the spin susceptibility in the even and odd channels, respectively, $J_{?}$ is the interlayer exchange coupling, $J_{q}=J\left(\cos q_{k}+\cos q_{y}\right)$ is the intralayer exchange. We here also include e to set the AF instability at =0.02 [4]. The mean-eld order parameters 0, 0 together with the chemical potential for different doping can be obtained from the self-consistent equations. The other parameters we choose are t = 2J, $t^{0}=0.45t$.

Before we present our results, we wish to point out that the above form ulas represent the spin susceptibility of the ferm ions. The spin susceptibility for physical electrons should be 2 due to the boson condensation in the superconducting state.

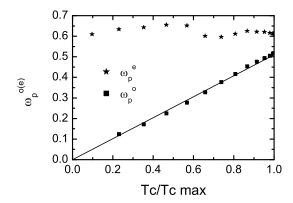


FIG .2: The resonance frequency as a function of the critical temperature T_{c} with t_{f} = 0.1J and J_{f} = 0.15J .

III. RESULTS AND DISCUSSION

The odd and even channel spin susceptibilities at different doping densities are shown in Figs.1(a) and (b), respectively. As seen, the peak intensity in the odd channel is sensitive to the doping, namely, it increases dramatically as the doping decreases. While in the even channel it increases slowly as the doping decreases. To see the doping evolution more clearly, we plot the peak positions of the even and odd channels as a function of the doping in Fig.1 (c), and the ratio of the intensities of the spin resonance between the even and odd channels, = $I^e = I^o$ versus doping in Fig.1 (d). From Fig.1 (c), the resonance frequency in the odd channel increases as the doping increases and saturates at the optimal doping, then it decreases slightly in the overdoped regime. W hile in the even channel, the resonance frequency increases as the doping decreases, so that the peak positions of the even and odd channels are closer and closer as the doping density increases, and the corresponding resonance frequencies are almost the same in the deeply overdoped sample. The dierence of the intensities in the even and odd channels increases as the doping density decreases, as seen in Fig.1 (d). The intensity ratio is only 0:1 in the strongly underdoped sample, and around 0.4 in the overdoped region. Our results are qualitatively consistent with the experim ental results [28]. We also exam ine the relationship between the resonance frequency and the critical tem perature T_c by using an empirical for $mula T_c=T_{cm ax} = 1 c($ $0:16)^2$, where c = 51 is used to ensure the AF instability to occur at = 0.02. The resonance frequency in the odd and even channels as a function of T_c is plotted in Fig.2 (0:16). The resonance frequency (! $_{\text{p}}^{\text{o}})$ is found to be proportional to T_{c} in the odd channel, which is in good agreem ent with the experim ental results [4, 5, 6]. While in the even channel, the spin resonance frequency (! $_{p}^{e}$) depends weakly on T $_{c}$ in the strongly underdoped sample, being also qualitatively consistent with the very recent experiments [28], in which the resonance frequency in the even channel is observed to increase in the overdoped sample and to sat-

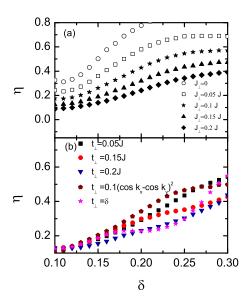


FIG. 3: (Color on line) (a) The intensity ratio of the spin resonance between the even and odd channels for dierent interlayer exchange coupling with $t_2=0.1J$. (b) The intensity ratio of the spin resonance between the even and odd channel for dierent interlayer hopping constants with $J_2=0.15J$.

urate to a constant in the underdoped sample.

We now address the dependence of the intensity difference of the spin resonance between the two channels on the parameters $t_{?}$ and $J_{?}$. The intensity ratio as a function of the doping for dierent J_2 is plotted in Fig.3(a). As seen, when J_2 increases, the intensity ratio decreases, indicating that the interlayer exchange coupling can strongly a ect the even and odd channels and enhance the di erence. However, the intensity ratio decreases as the doping decreases for all J? we considered, indicating that our results presented above are robust against the variation of the interlayer exchange coupling $J_{?}$. On the other hand, we can also see from Fig.3(a) that even if $J_2 = 0$, the intensity in the odd channel is still signi cantly stronger than that in the even channel, suggesting that the interlayer exchange coupling is not the only contribution for the di erence between the two channels. In fact, the other contribution comes from the interlayer single-particle hopping. To show this, we plot the ratio versus the doping for dierent hopping constantst, in Fig.3 (b). Ast, increases, the ratio decreases. So, the interlayer single particle hopping also contributes to enhance the di erence between the two channels. Let us also consider the cases that to depends on the doping density ($t_{?}$ /) and m om entum [$t_{?}$ / ($cosk_{x}$ $cosk_{y}$)²]. Note that, the bilayer splitting is found to be momentum dependence in Bi-2212 bilayer system s [31], without observing the bilayer splitting in the nodal direction. We also exam ined that our results are robust for dierent types of the interlayer hopping constant to, as shown in Fig.3(b).

Now we elaborate the origin of the above features based on the Ferm i surface topology. In Fig. 4 [32], we plot the

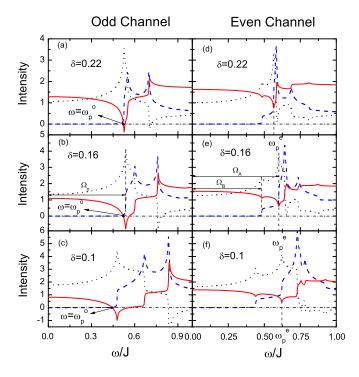


FIG. 4: (Color on line) The bare spin susceptibilities versus the frequency! at dierent doping densities in the odd and even channels with the quasiparticle damping = 0.002. The dotted lines denote the real parts and the dashed lines in aginary parts, respectively. The solid lines are the real parts of the RPA factor [l + $(J_Q J_?)$ Re $_0^{e(o)}$ (Q;!)=2] (scaled 2) with signs for the even and odd channels, respectively.

im aginary and real parts of the bare spin susceptibility $_{\circ}^{\mathrm{(e)}}$ in the odd and even channels with dierent doping densities. We rst address the spin excitation in the odd channel. As shown in Fig.4 (a-c), the imaginary part of the bare spin susceptibility approaches to zero as the frequency is below the spin gap. At the edge of the spin gap, it has a step-like rise which arises from the at band near (;0) (Van Hove singularity). As a result, the realpart of the bare spin susceptibility Re $^{\circ}_{0}$ develops a sharp structure near the edge. Consequently, a pole occurs when the real part of the RPA factor $1 + (eJ_0)$ $J_?$)Re $^{\circ}=2$ is equal to zero at the frequency $!^{\circ}_{\mathfrak{p}}$ (slightly below the gap edge) and in the meantime the imaginary part of the spin susceptibility at $!_{p}^{\circ}$ approaches to zero due to the spin gap. This suggests the formation of a spin collective mode, which is ascribed to be the spin resonance. We can also see from Fig.4 (a-c) that the frequency, at which a step-like rise occurs, increases as the doping decreases starting from the optim aldoping, but it decrease slightly in the overdoped regime. This explains the doping dependence of the resonance frequency as presented in Fig.1 (c). On the other hand, the real part of the bare spin susceptibility also increases with the decrease of doping. This leads to the pole position to be more and more below the spin gap edge (due to the nite damping the imaginary part of ${\circ}_0$ is not zero slightly below the

spin gap) and consequently to an increase in the renormalized spin susceptibility. For the even channel case, an obvious di erence is seen from Fig.4 (d-f) that there are two step-like rises, instead of one in the odd channel. These two step-like rises come from the particle-hole scattering in the B and A bands, respectively, because the spin susceptibility in the even channel is contributed by the intra-band A! A and B! B scatterings as shown clearly in Eq.(4). The scattering within the B band leads to the step-like rise in $^{\rm e}_{\rm 0}$ at a lower frequency $_{\rm B}$, while that in the A band leads to a higher frequency rise at $_{A}$. Since the rise is larger at $_{
m A}$, the corresponding enhancem ent of the real part of ${\,}^{\rm e}_{0}$ is larger there. Thus, the spin resonance peak occurs near $\,$ $_{\text{A}}$ in this case. We note that, due to a smaller vertex $eJ_Q + J_?$ in this channel, the pole condition $1 + (eJ_Q + J_P)Re_0^e = 2 = 0$ could not be satis ed at a large doping range. In the meantime, the corresponding imaginary part of 0 is of appreciable value because of the scattering in the B band. So, the resonance peak in this case is basically a quasi-resonance peak, with its intensity being much lower than that in the odd channel as shown in Fig.1 (b). Also in contrast to the case of the odd channel, the frequency, at which the high-energy step-like rise occurs, increases with the decrease of doping. Therefore, the spin resonance frequency at the even channel increases upon reducing the doping as shown in Fig.1(c). On the other hand, one can see from Fig.4 (d-f) that both the real and im aginary parts of $_0^e$ in the lower side of $_A$ do not change much with doping. Considering the appreciable increase of the resonance intensity with the decrease of doping in the odd channel, it is expected that the di erence between the spin resonance peak intensities of the two channels increases as the doping decreases.

These features can be traced to the evolution of the Ferm i surface with doping. We present the normal state Ferm i surface in Fig.5. As discussed above, the step-like rise is near the spin gap edge. In the zero temperature lim it, the bare spin susceptibility [Eq.(3)] can be rewritten as Im (; °) (q;!) / (; °) (k;q)). Here, (! (; °) (k;q) = $E_k^{()} + E_{k+q}^{(0)}$ denotes the energy to break a pair and excite two quasiparticles from the superconducting condensed state, and has a minimum of the exciting energy (M $\mathbb{N}_k[$ (; $^{\circ})$ (k;q)]) when the wave vector q is at Q = (;) where the spin resonance is observed, which is just the spin gap. Because of the d-w ave sym m etry of the superconducting gap and energy band structure, the excitation within the A band with the minimum excitation energy is the M 0-to-M excitation as shown in Fig.5(a), while that within the B band and that of the interband correspond respectively to the N 0-to-N and O 0-to-O excitations, where M; M°; N; N° are the crossing points (hot spot) of the Ferm i surface with the magnetic Brillouin zone boundary, and 0 (0 $^{\circ}$) are the crossing points of the B (A) band Ferm i surface with the (;) shifted im ages of the A (B) band Ferm i surface. From Fig.5 (b), we can see that the hot spot of the B band m oves towards the nodal direction as the doping decreases, and consequently

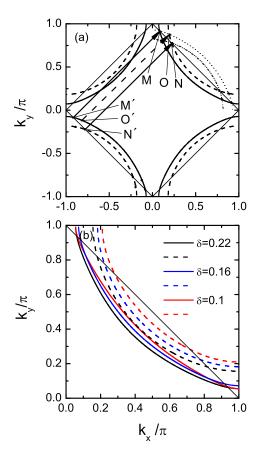


FIG. 5: (Color on line) (a) The norm al state Ferm i surface at the doping = 0.16 with t = 0.1J. The bold solid and dashed lines are the Ferm i surface of the A and B bands, respectively. The dotted and the dash-dotted lines in the 1st quadrant are the (;) shifted in ages of the A and B band Ferm i surfaces in the third quadrant. The solid and dashed arrows denote the intraband and interband scatterings, respectively. (b) The Ferm i surfaces of the A (solid lines) and B bands (dashed lines) in the 1st quadrant of the B rillouin zone at diesent doping densities.

the magnitude of the corresponding superconducting gap decreases. The A band depends weakly on the doping density, but the magnitude of the superconducting gap

increases with doping, as calculated from the mean-eld theory here and observed in experiments [33]. Because the spin excitation in the odd channel comes from the 0 $^0\text{-to-O}$ excitation, its spin gap decreases with the decrease of doping. While, the high-energy step-like rise in the even channel is contributed by the excitation from M 0 to M , it increases with the decrease of doping.

IV. SUMMARY

In sum mary, we have exam ined the doping evolution of the spin susceptibility in the even and odd channels in the bilayer high-T_c superconducting materials based on the bilayer t J type model. In the bonding and antibonding band representation, there exist two channels of the spin excitation according to the intraband scattering and interband scattering. Each channel has its distinct resonant mode. In the odd channel, i.e., the interband scattering, the spin susceptibility shows a strong doping dependence. As the doping decreases, the intensity increases dram atically and the resonance frequency is linear with T_c. The resonance frequency in the even channel approaches to that in the odd channel and the ratio between the two channels is around 0.4 in the overdoped region. As the doping decreases, the resonance frequency increases and saturates at the strongly underdoped sam ple. In addition, it has been found that the di erences of the resonance positions and intensities between the two channels are enlarged as the doping decreases. Our results are well consistent with the experiments. We have elaborated the results based on the topology of the Ferm i surface and the d-wave superconductivity.

A cknow ledgm ents

The work was supported by the RGC grants of Hong Kong (HKU 7050/03P and HKU-3/05C), the NSFC (10174019,10334090,10429401 and 10525415), and the 973 project under the Grant No 2006CB 601002.

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